

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph 70 on page 16 with the following paragraph.

[0070] A schematic diagram of an exemplary pixel cell 700 according to an embodiment of the invention is shown in FIG. 7. Pixel cell 700 is formed as described above in connection with FIGS. 2-6. Illustratively, the CMOS pixel cell 700 is a four transistor (4T) cell. Pixel cell 700 comprises a photodiode 720. Pixel cell 700 also includes a transfer gate ~~760~~ 730 for transferring photo-generated and amplified charge from photodiode 720 to a sensing node, which is illustratively a floating diffusion region 705. The floating diffusion region 705 is electrically connected to the gate of an output source follower transistor 732. The pixel cell 700 also includes a reset transistor having a gate 731 for resetting the floating diffusion region 705 to a predetermined voltage before sensing a signal. Source follower transistor 732 receives at its gate an electrical signal from the floating diffusion region 705. There is also a row select transistor 733 for outputting a signal from the source follower transistor 723 to an output terminal in response to an address signal. Source follower transistor and row select transistor serve as readout circuitry for pixel cell 700.